

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently amended) An electronic device comprising:
a first insulating film formed on a substrate, a conductive film containing silicon and carbon; and a hole formed in the first insulating film, and
wherein the first insulating film includes silicon and carbon, and the first insulating film has ~~having~~ a density varying gradually in a direction of a thickness thereof.
2. (Original) The electronic device of claim 1, wherein an uppermost portion of the first insulating film has a density higher than an average density of the first insulating film.
3. (Original) The electronic device of claim 2, wherein the density of the uppermost portion is 1.8 g/cm^3 or more and the average density is 1.4 g/cm^3 or less.
4. (Original) The electronic device of claim 1, wherein a lowermost portion of the first insulating film has a density higher than an average density of the first insulating film.
5. (Original) The electronic device of claim 4, wherein the density of the lowermost portion is 1.8 g/cm^3 or more and the average density is 1.4 g/cm^3 or less.
6. (Original) The electronic device of claim 1, further comprising:
a second insulating film formed on the first insulating film, wherein
an average density of the second insulating film is 1.5 g/cm^3 or more and 1.7 g/cm^3 or less.

7. (Original) The electronic device of claim 1, further comprising:
a second insulating film formed on the first insulating film, wherein
an abundance ratio of oxygen to silicon each contained in a portion of the second
insulating film located adjacent to the first insulating film is less than 2.

8. (Currently amended) An electronic device comprising:
a first insulating film formed on a substrate, a conductive film containing silicon and
~~carbon, and a hole~~ formed in the first insulating film, and
wherein the first insulating film includes silicon and carbon, and the first insulating film
has ~~having~~ a carbon concentration varying gradually in a direction of a thickness thereof.

9. (Original) The electronic device of claim 8, wherein an uppermost portion of the
first insulating film has a carbon concentration higher than an average carbon concentration of
the first insulating film.

10. (Original) The electronic device of claim 9, wherein the carbon concentration of
the uppermost portion is 30 at% or more and the average carbon concentration is 20 at% or less.

11. (Original) The electronic device of claim 8, wherein a lowermost portion of the
first insulating film has a carbon concentration higher than an average carbon concentration of
the first insulating film.

12. (Original) The electronic device of claim 11, wherein the carbon concentration of
the lowermost portion is 30 at% or more and the average carbon concentration is 20 at% or less.

13. (Original) The electronic device of claim 8, further comprising:
a second insulating film formed on the first insulating film, wherein
an average density of the second insulating film is 1.5 g/cm^3 or more and 1.7 g/cm^3 or
less.

14. (Original) The electronic device of claim 8, further comprising:
a second insulating film formed on the first insulating film, wherein
an abundance ratio of oxygen to silicon each contained in a portion of the second
insulating film adjacent to the first insulating film is less than 2.

15-24. (Cancelled)